

# Preface

This special edition presents recent technological advances, research results, and engineering solutions in substrate and epitaxial layer manufacturing, addressing the fundamental and technological aspects underpinning modern manufacturing of power electronic devices based on silicon carbide and gallium nitride. The articles highlight a broad spectrum of topics, ranging from epitaxial layer growth and crystal growth to substrate finishing technologies that ensure the final products' high structural and electronic properties.

The special edition aims to serve as a valuable resource for researchers and engineers engaged in developing and producing advanced semiconductor power devices, and provides readers with a balanced view of the scientific foundations and applied methodologies in this field.